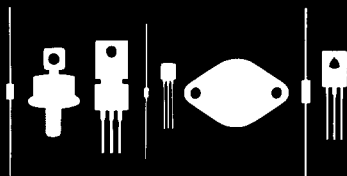


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145 Adams Avenue
Hauppauge, New York 11788



2N524 THRU 2N527

PNP GERMANIUM TRANSISTORS

JEDEC TO-5 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N524 series types are germanium PNP transistors designed for low frequency medium power amplifier and switching applications.

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNIT
Collector-Base Voltage	V _{CB0}	45	V
Collector-Emitter Voltage	V _{CER}	30	V
Emitter-Base Voltage	V _{EBO}	15	V
Collector Current	I _C	500	mA
Emitter Current	I _E	500	mA
Power Dissipation	P _D	225	mW
Operating and Storage			
Junction Temperature	T _J T _{STG}	-65 to +100	°C
Thermal Resistance	θ _{JA}	33.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I _{CB0}	V _{CB} =30V		10	μA
I _{EBO}	V _{EB} =15V		10	μA
BV _{CB0}	I _C =200μA	45		V
BV _{CER}	I _C =600μA, R _{BE} =10kΩ	30		V
V _{CE} (SAT)	I _C =20mA, I _B =2.0mA (2N524)		130	mV
V _{CE} (SAT)	I _C =20mA, I _B =1.33mA (2N525)		130	mV
V _{CE} (SAT)	I _C =20mA, I _B =1.0mA (2N526)		130	mV
V _{CE} (SAT)	I _C =20mA, I _B =0.67mA (2N527)		130	mV
V _{BE} (ON)	V _{CE} =1.0V, I _C =20mA (2N524)	220	320	mV
V _{BE} (ON)	V _{CE} =1.0V, I _C =20mA (2N525)	200	300	mV
V _{BE} (ON)	V _{CE} =1.0V, I _C =20mA (2N526)	190	280	mV
V _{BE} (ON)	V _{CE} =1.0V, I _C =20mA (2N527)	180	260	mV
h _{FE}	V _{CE} =1.0V, I _C =20mA (2N524)	25	42	
h _{FE}	V _{CE} =1.0V, I _C =20mA (2N525)	34	65	
h _{FE}	V _{CE} =1.0V, I _C =20mA (2N526)	53	90	
h _{FE}	V _{CE} =1.0V, I _C =20mA (2N527)	72	121	
C _{ob}	V _{CB} =5.0V, I _C =0, f=1.0MHz	5.0	40	pF
NF	V _{CB} =5.0V, R _G =1.0kΩ, BW=1.0Hz, f=1.0kHz	-	15	db

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